

SN74HC7032 Quadruple 2-Input OR Gates with Schmitt-Trigger Inputs

1 Features

- Wide Operating Voltage Range: 2 V to 6 V
- Outputs Can Drive Up To 10 LSTTL Loads
- Low Power Consumption, 20- μ A Maximum I_{CC}
- Operation from very slow input transitions
- ± 4 -mA Output Drive at 5 V
- Low Input Current of 1 μ A

2 Applications

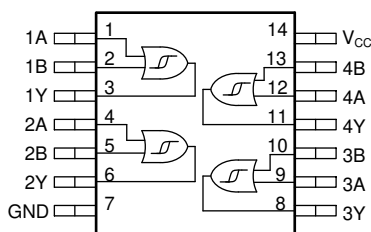
- [Use fewer inputs to monitor error signals](#)
- [Combine active-low enable signals](#)

3 Description

This device contains four independent 2-input OR Gates with Schmitt-trigger inputs. Each gate performs the Boolean function $Y = A + B$ in positive logic.

Device Information¹

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74HC7032N	PDIP (14)	19.30 mm × 6.40 mm
SN74HC7032D	SOIC (14)	8.70 mm × 3.90 mm



Functional pinout of the SN74HC7032

¹ #none#



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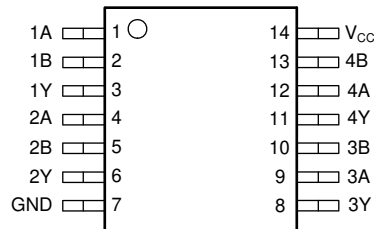
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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision E (November 2004) to Revision F (June 2019)	Page
• Updated to new data sheet standards.....	1
• Updated the number format for tables, figures, and cross-references throughout the document.....	1
• $R_{\theta JA}$ increased for the D (86 to 133.6 °C/W) and decreased for the N package (80 to 61.4 °C/W).....	4

5 Pin Configuration and Functions



**Figure 5-1. D or N Package
 14-Pin SOIC or PDIP
 Top View**

Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1A	1	Input	Channel 1, Input A
1B	2	Input	Channel 1, Input B
1Y	3	Output	Channel 1, Output Y
2A	4	Input	Channel 2, Input A
2B	5	Input	Channel 2, Input B
2Y	6	Output	Channel 2, Output Y
GND	7	—	Ground
3Y	8	Output	Channel 3, Output Y
3A	9	Input	Channel 3, Input A
3B	10	Input	Channel 3, Input B
4Y	11	Output	Channel 4, Output Y
4A	12	Input	Channel 4, Input A
4B	13	Input	Channel 4, Input B
V _{CC}	14	—	Positive Supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	-0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	V _I < -0.5 V or V _I > V _{CC} + 0.5 V		±20 mA
I _{OK}	Output clamp current ⁽²⁾	V _O < -0.5 V or V _O > V _{CC} + 0.5 V		±20 mA
I _O	Continuous output current	V _O = 0 to V _{CC}		±25 mA
	Continuous current through V _{CC} or GND			±50 mA
T _J	Junction temperature ⁽³⁾			150 °C
T _{stg}	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) Guaranteed by design.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	2	5	6	V
V _I	Input voltage	0		V _{CC}	V
V _O	Output voltage	0		V _{CC}	V
T _A	Operating free-air temperature	SN74HC00		-40	85 °C

6.4 Operating Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

PARAMETER		TEST CONDITIONS	V _{CC}	MIN	TYP	MAX	UNIT
C _{pd}	Power dissipation capacitance per gate	No load	2 V to 6 V		20		pF

6.5 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74HC7032		UNIT
		N (PDIP)	D (SOIC)	
		14 PINS	14 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	61.4	133.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	49.2	89.0	°C/W

THERMAL METRIC ⁽¹⁾		SN74HC7032		UNIT
		N (PDIP)	D (SOIC)	
		14 PINS	14 PINS	
R _{θJB}	Junction-to-board thermal resistance	41.2	89.5	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	28.8	45.5	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	40.9	89.1	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.6 Electrical Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

PARAMETER		TEST CONDITIONS		V _{CC}	Operating free-air temperature (T _A)						UNIT
					25°C			-40°C to 85°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{T+}	Positive switching threshold			2 V	0.7	1.2	1.5	0.7		1.5	V
				4.5 V	1.55	2.5	3.15	1.55		3.15	
				6 V	2.1	3.3	4.2	2.1		4.2	
V _{T-}	Negative switching threshold			2 V	0.3	0.6	1	0.3		1	V
				4.5 V	0.9	1.6	2.45	0.9		2.45	
				6 V	1.2	2	3.2	1.2		3.2	
ΔV _T	Hysteresis (V _{T+} - V _{T-})			2 V	0.2	0.6	1.2	0.2		1.2	V
				4.5 V	0.4	0.9	2.1	0.4		2.1	
				6 V	0.5	1.3	2.5	0.5		2.5	
V _{OH}	High-level output voltage	V _I = V _{IH} or V _{IL}	I _{OH} = -20 μA	2 V	1.9	1.998		1.9			V
				4.5 V	4.4	4.499		4.4			
			6 V	5.9	5.999		5.9				
			I _{OH} = -4 mA	4.5 V	3.98	4.3		3.84			
I _{OH} = -5.2 mA	6 V	5.48	5.8		5.34						
V _{OL}	Low-level output voltage	V _I = V _{IH} or V _{IL}	I _{OL} = 20 μA	2 V		0.002	0.1			0.1	V
				4.5 V		0.001	0.1		0.1		
			6 V		0.001	0.1		0.1			
			I _{OL} = 4 mA	4.5 V		0.17	0.26		0.33		
I _{OL} = 5.2 mA	6 V		0.15	0.26		0.33					
I _I	Input leakage current	V _I = V _{CC} or 0		6 V		±0.1	±100			±1000	nA
I _{CC}	Supply current	V _I = V _{CC} or 0	V _I = V _{CC} or 0	6 V			2			20	μA
C _i	Input capacitance			2 V to 6 V		3	10			10	pF

6.7 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM	TO	V_{CC}	Operating free-air temperature (T_A)						UNIT
				25°C			-40°C to 85°C			
				MIN	TYP	MAX	MIN	TYP	MAX	
t_{pd}	Propagation delay	A or B	Y	2 V	60	130	163			ns
				4.5 V	18	26	33			
				6 V	14	22	28			
t_t	Transition-time	Any	2 V	28	75	95			ns	
			4.5 V	8	15	19				
			6 V	6	13	16				

6.8 Typical Characteristics

$T_A = 25^\circ\text{C}$

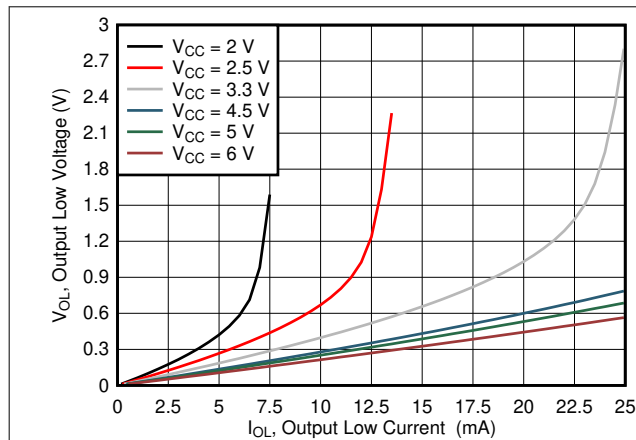


Figure 6-1. Typical output low voltage versus sink current across common supply values

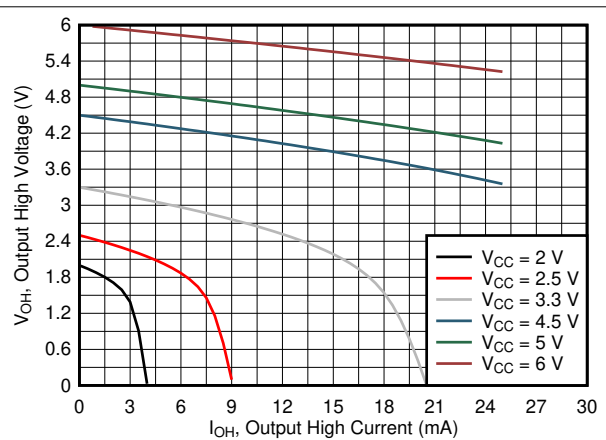


Figure 6-2. Typical output high voltage versus source current across common supply values

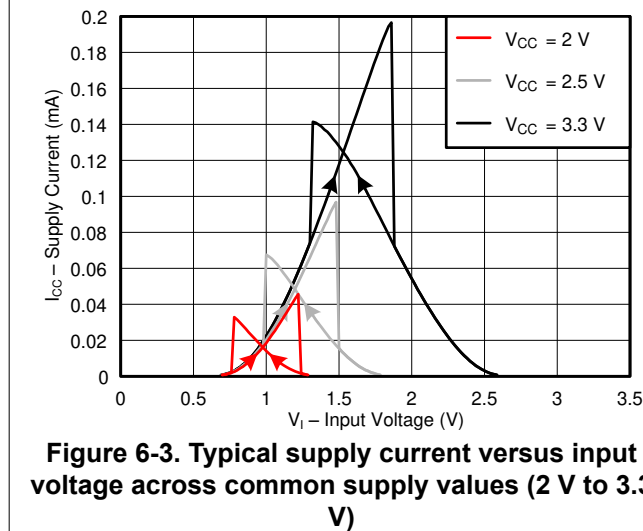


Figure 6-3. Typical supply current versus input voltage across common supply values (2 V to 3.3 V)

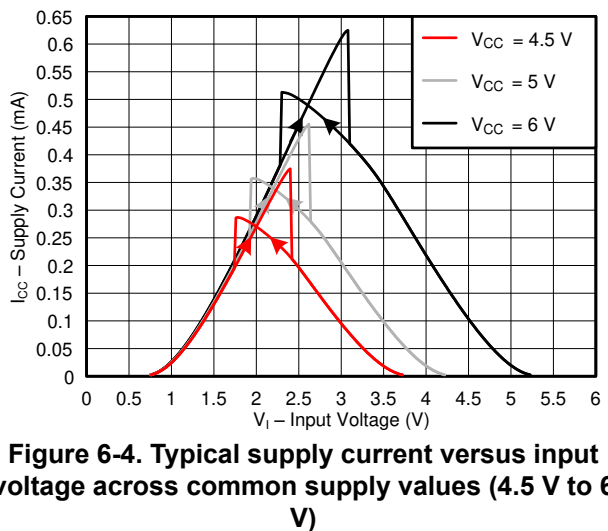
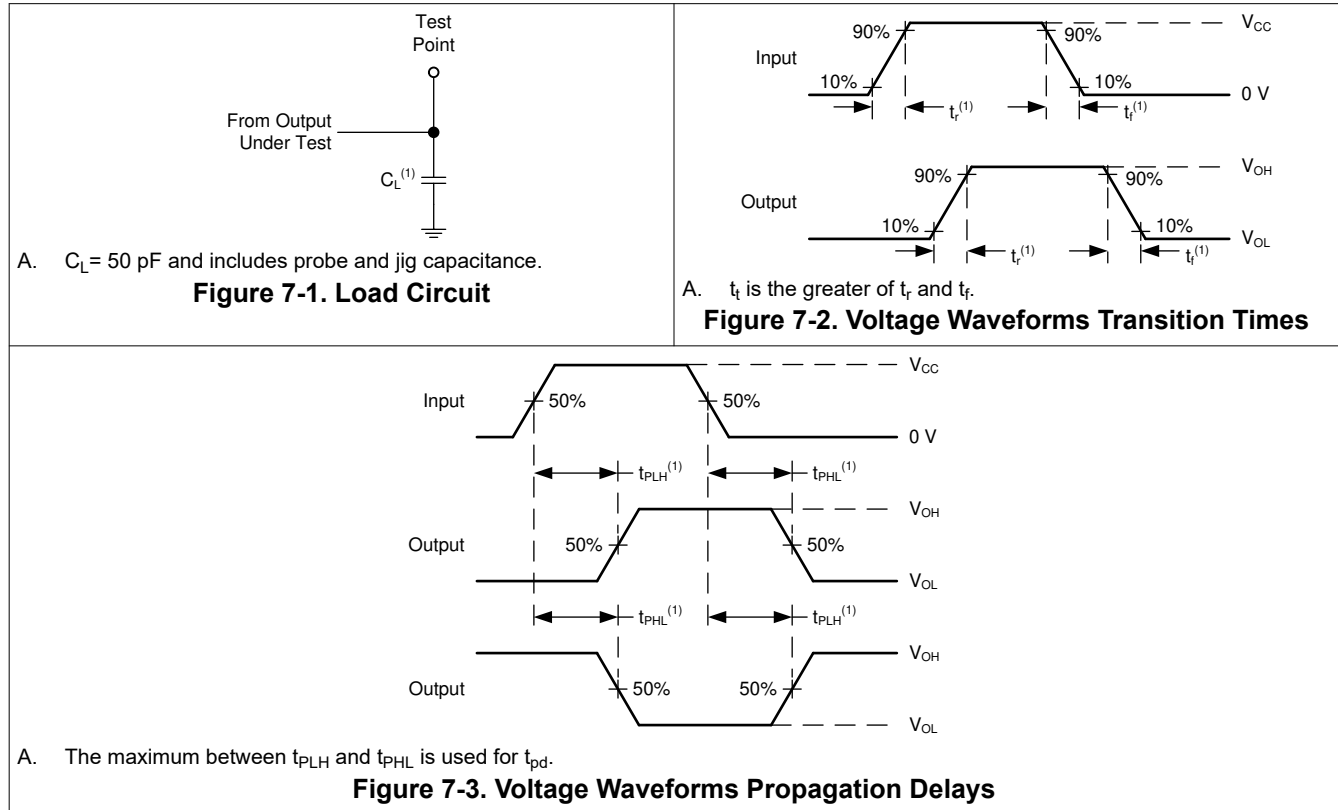


Figure 6-4. Typical supply current versus input voltage across common supply values (4.5 V to 6 V)

7 Parameter Measurement Information

- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1 \text{ MHz}$, $Z_O = 50 \Omega$, $t_t < 6 \text{ ns}$.
- The outputs are measured one at a time, with one input transition per measurement.

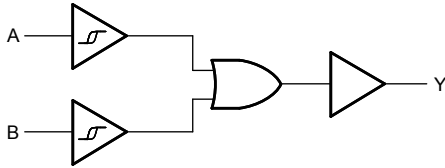


8 Detailed Description

8.1 Overview

This device contains four independent 2-input OR Gates with Schmitt-trigger inputs. Each gate performs the Boolean function $Y = A + B$ in positive logic.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Balanced CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to over-current. The electrical and thermal limits defined in the [Absolute Maximum Ratings](#) table must be followed at all times.

8.3.2 CMOS Schmitt-Trigger Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the [Electrical Characteristics](#) table. The worst case resistance is calculated with the maximum input voltage, given in the [Absolute Maximum Ratings](#) table, and the maximum input leakage current, given in the [Electrical Characteristics](#) table, using ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the [Electrical Characteristics](#) table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs slowly will also increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see [Understanding Schmitt Triggers](#).

8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in [Figure 8-1](#).

CAUTION

Voltages beyond the values specified in the [Section 6.1](#) table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

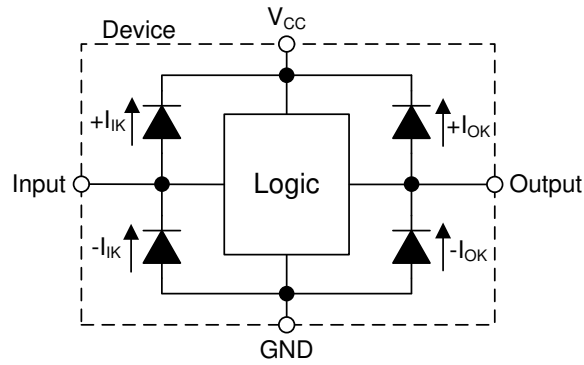


Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

Table 8-1. Function Table

INPUTS		OUTPUT Y
A	B	
H	X	H
X	H	H
L	L	L

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

In this application, three 2-input OR gates are combined to produce a 4-input OR gate function as shown in [Figure 9-1](#). The fourth gate can be used for another application in the system, or the inputs can be grounded and the channel left unused.

The SN74HC7032 is used to directly control the Enable pin of a fan driver. The fan driver requires only one input signal to be HIGH before being enabled, and should be disabled in the event that all signals go LOW. The 4-input OR gate function combines the four individual overhear signals into a single active-high enable signal.

Temperature sensors can often be spread throughout a system rather than being in a centralized location. This would mean longer length traces or wires to pass signals through leading to slower edge transitions. This makes the SN74HC7032 ideal for the application since it has Schmitt-trigger inputs that do not have input transition rate requirements.

9.2 Typical Application

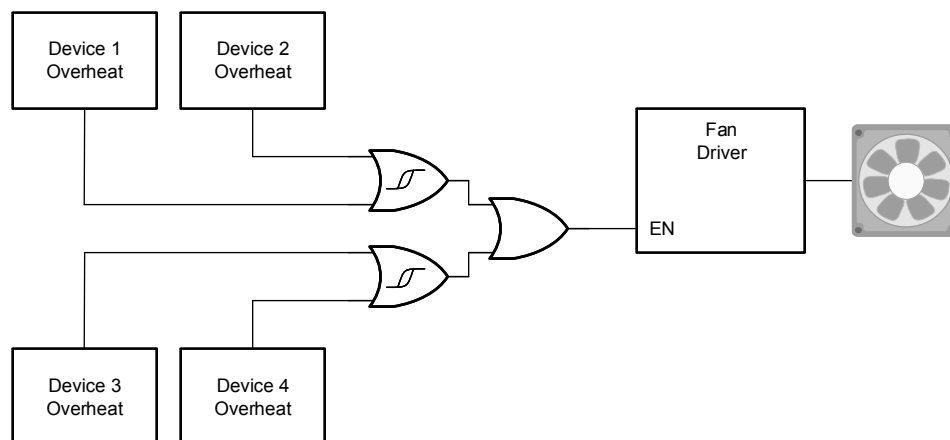


Figure 9-1. Typical application block diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the maximum static supply current, I_{CC} , listed in *Electrical Characteristics* and any transient current required for switching.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HC7032 plus the maximum supply current, I_{CC} , listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HC7032 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 50 pF.

The SN74HC7032 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OL} . When outputting in the high state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross to be considered a logic LOW, and to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HC7032, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to *Feature Description* section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HC7032 to the receiving device(s).
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

9.2.3 Application Curves

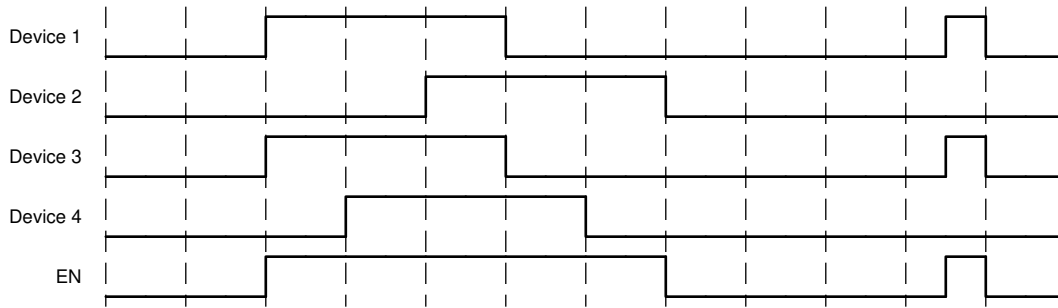


Figure 9-2. Application timing diagram

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μF and 1- μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or VCC, whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

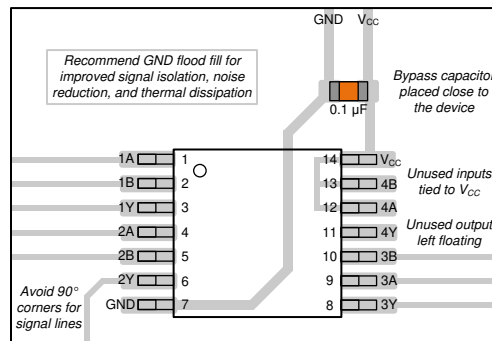


Figure 11-1. Example layout for the SN74HC7032

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- [HCMOS Design Considerations](#)
- [CMOS Power Consumption and CPD Calculation](#)
- [Designing with Logic](#)

12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

Table 12-1. Related Links

PARTS	PRODUCT FOLDER	ORDER NOW	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN54HC7032	Click here	Click here	Click here	Click here	Click here
SN74HC7032	Click here	Click here	Click here	Click here	Click here

12.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

12.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74HC7032D	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC7032	Samples
SN74HC7032DT	LIFEBUY	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC7032	
SN74HC7032N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HC7032N	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HC7032DT	SOIC	D	14	250	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HC7032DT	SOIC	D	14	250	210.0	185.0	35.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN74HC7032D	D	SOIC	14	50	506.6	8	3940	4.32
SN74HC7032N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC7032N	N	PDIP	14	25	506	13.97	11230	4.32

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 -  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 -  Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AB.

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



4211283-3/E 08/12

- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



4040049/E 12/2002

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - (C) Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - (D) The 20 pin end lead shoulder width is a vendor option, either half or full width.

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